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Terms	Documents
118 and 119	22

Database: US Patents Full-Text Database ▲
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Refine Search:

118 and 119

[Clear](#)**Search History****Today's Date: 5/31/2001**

<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
USPT	l18 and l19	22	<u>L20</u>
USPT	rf adj4 bias	1591	<u>L19</u>
USPT	l16 and l17	143	<u>L18</u>
USPT	chamber or reactor	555311	<u>L17</u>
USPT	l15 and l10	167	<u>L16</u>
USPT	l14 and l9	379	<u>L15</u>
USPT	l13 and l8	510	<u>L14</u>
USPT	l12 and l4	11213	<u>L13</u>
USPT	l1 and l11	14304	<u>L12</u>
USPT	l2 or l3	20093	<u>L11</u>
USPT	bias	223158	<u>L10</u>
USPT	electrode\$1	260278	<u>L9</u>
USPT	l7 near8 plasma	4233	<u>L8</u>
USPT	l5 or l6	360666	<u>L7</u>
USPT	"N.sub.2"	85985	<u>L6</u>
USPT	nitrogen	326793	<u>L5</u>
USPT	oxide\$1	413343	<u>L4</u>
USPT	reactive adj3 ion adj3 etch\$5	14724	<u>L3</u>
USPT	RIE	13350	<u>L2</u>
USPT	semiconduct\$4	225749	<u>L1</u>